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Silicon Carbide (SiC) Schottky Diode – EliteSiC, 50 A, 1200 V, D3, TO-247-2L

NDSH50120C

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

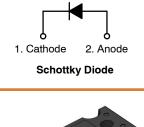
Features

- Max Junction Temperature 175°C
- Avalanche Rated 380 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Halogen Free/BFR Free and are RoHS Compliant

Applications

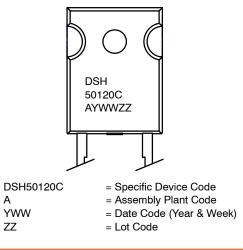
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits







MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NDSH50120C

Symbol	Parameter		Value	Unit
V _{RRM}	Peak Repetitive Reverse Voltage		1200	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		380	mJ
١ _F	Continuous Rectified Forward Current @ T _C < 139°C		50	А
	Continuous Rectified Forward Current @ $T_C < T_C$	ntinuous Rectified Forward Current @ $T_C < 135^{\circ}C$		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1568	A
		T _C = 150°C, 10 μs	1414	A
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	231	A
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	84	A
Ptot	Power Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$	375	W
		T _C = 150°C	62.5	W
TJ, T _{STG}	Operating and Storage Temperature Range		–55 to +175	°C

ABSOLUTE MAXIMUM RATINGS (T_J = 25° C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. E_{AS} of 380 mJ is based on starting $T_J = 25^{\circ}$ C, L = 0.5 mH, $I_{AS} = 39$ A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.4	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient, Max	40	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted)

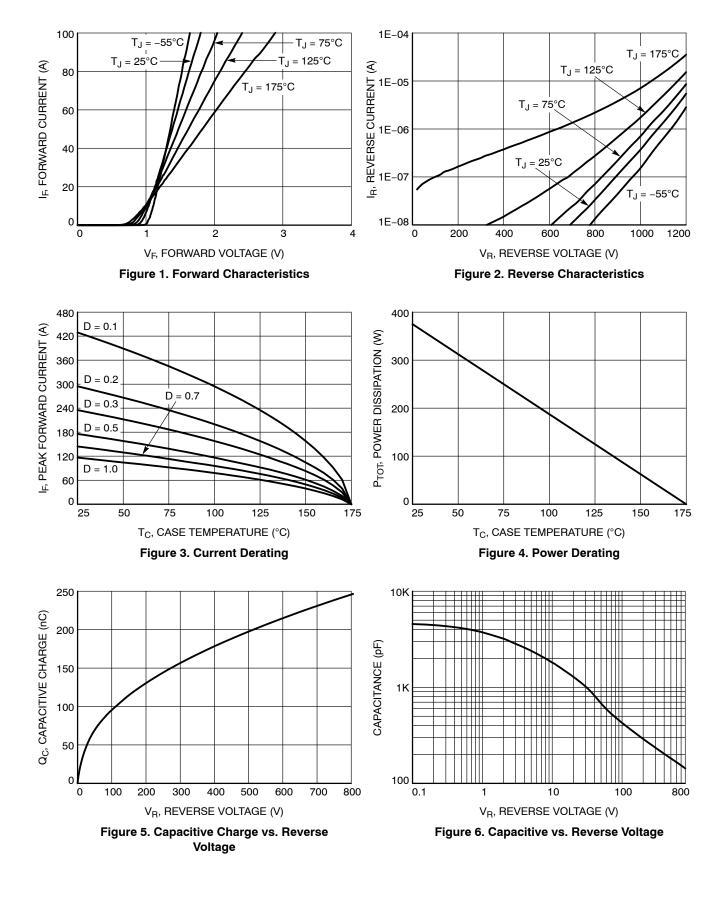
Symbol	Parameter	Test Condition	Min	Тур	Мах	Unit
V _F	Forward Voltage	I _F = 50 A, T _J = 25°C	-	1.4	1.75	V
		I _F = 50 A, T _J = 125°C	-	1.63	-	
		I _F = 50 A, T _J = 175°C	-	1.84	-	
I _R	Reverse Current	$V_{\rm R}$ = 1200 V, $T_{\rm J}$ = 25°C	-	12.2	200	μΑ
		V_{R} = 1200 V, T_{J} = 125°C	-	30	200	
		$V_{R} = 1200 \text{ V}, \text{ T}_{J} = 175^{\circ}\text{C}$	-	61.5	200	
Q_{C}	Total Capacitive Charge	V = 800 V	-	246	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	3691	-	pF
		V _R = 400 V, f = 100 kHz	-	198	-	
		V _R = 800 V, f = 100 kHz	-	143	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
NDSH50120C	DSH50120C	TO-247-2LD (Pb-Free / Halogen Free)	30 Units / Tube

NDSH50120C



TYPICAL CHARACTERISTICS (T_J = 25°C UNLESS OTHERWISE NOTED)

NDSH50120C

TYPICAL CHARACTERISTICS (T_J = 25°C UNLESS OTHERWISE NOTED)

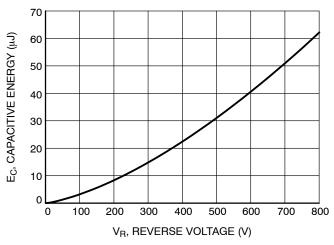


Figure 7. Capacitance Stored Energy

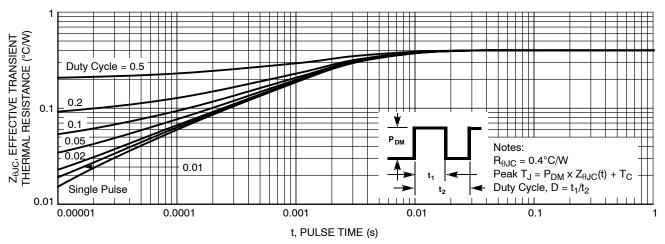
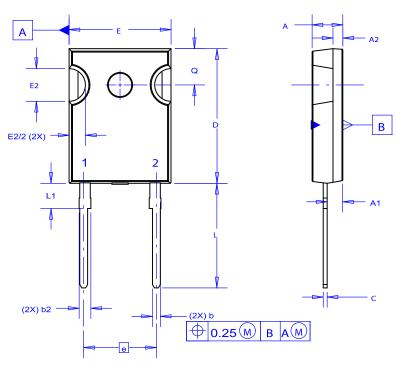


Figure 8. Junction-to-Case Transient Thermal Response Curve

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TO-247-2LD CASE 340DA ISSUE A

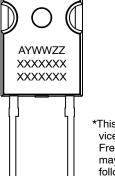
DATE 27 FEB 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD
- FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.





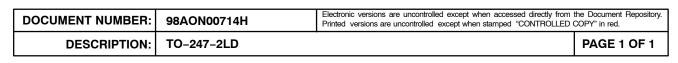
XXXXX	= Specific Device Code
А	= Assembly Location
Υ	= Year

WW = Work

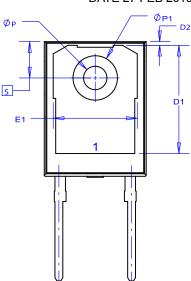
ΖZ

V = Work Week = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.



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	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	4.58	4.70	4.82	
A1	2.20	2.40	2.60	
A2	1.40	1.50	1.60	
b	1.17	1.26	1.35	
b2	1.53	1.65	1.77	
С	0.51	0.61	0.71	
D	20.32	20.57	20.82	
D1	13.08	~	~	
D2	0.51	0.93	1.35	
E	15.37	15.62	15.87	
E1	12.81	~	~	
E2	4.96	5.08	5.20	
е	~	11.12	~	
L	15.75	16.00	16.25	
L1	3.69	3.81	3.93	
ØР	3.51	3.58	3.65	
Ø P1	6.60	6.80	7.00	
Q	5.34	5.46	5.58	
S	5.34	5.46	5.58	

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